

Al-Mustaqbal University / College of Engineering & Technology
Department (Communication Technical Engineering)

Class (First)

Subject (ELECTRONIC CIRCUITS) / Code (UOMU028022)

Lecturer (Prof.Dr.Haider J Abd)

2nd term – Lecture No. & Lecture Name (Lec4: Voltage-Feedback Bias Circuit)

4. Voltage-Feedback Bias Circuit:

Fig. 9-7a shows a voltage-feedback bias circuit.

Analysis:

- For the input (base-emitter circuit) loop as shown in Fig. 9-7b:

$$+V_{CC} - I'_C R_C - I_B R_B - V_{BE} - I_E R_E = 0$$

$$I'_C = I_C + I_B = I_E \cong I_C = \beta I_B$$

$$+V_{CC} - \beta I_B R_C - I_B R_B - V_{BE} - \beta I_B R_E = 0 \quad [9.11a]$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)(R_C + R_E)}$$

- For the output (collector-emitter circuit) loop as shown in Fig. 9-7c:

$$+I_E R_E + V_{CE} + I'_C R_C - V_{CC} = 0$$

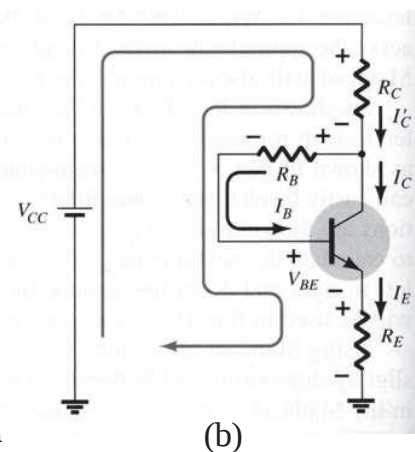
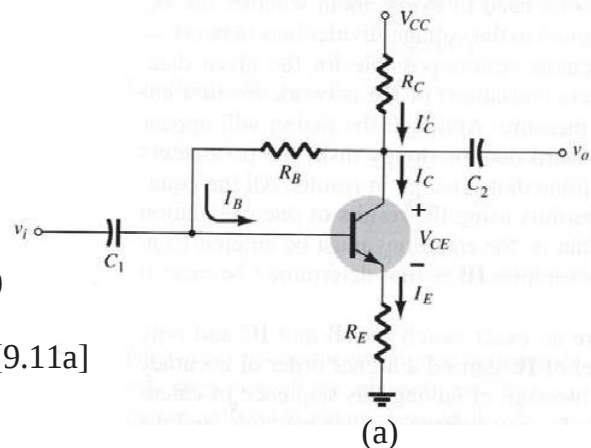
$$I'_C = I_E \cong I_C$$

$$V_{CE} = V_{CC} - I_C (R_C + R_E) \quad [9.11b]$$

Load-Line Analysis:

Continuing with the approximation $I'_C = I_C$ will result

in the same load line defined for the voltage-divider and emitter-biased configurations. The levels of I_{BQ} will be defined by the chosen base configuration.



Design:

For an optimum design:

$$\begin{aligned} V_{CEQ} &= \frac{1}{2} V_{CC} \\ I_{CQ} &= \frac{1}{2} I_{C(sat)} = \frac{V_{CC}}{2(R_C + R_E)} \\ V_E &= \frac{1}{10} V_{CC} \\ R_B &\leq \beta(R_C + R_E) \end{aligned}$$

[9-12]

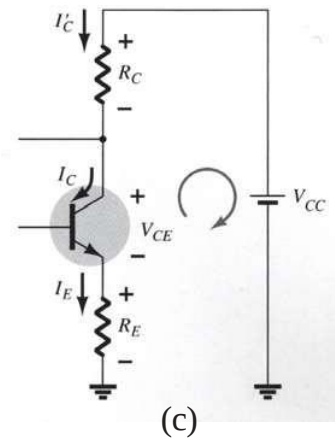


Fig. 9-7

Other Biasing Circuits:

Example 9-2: (Negative Supply)

Determine V_C and V_B for the circuit of Fig. 9-8.

Solution:

$$-I_B R_B - V_{BE} + V_{EE} = 0 \quad (\text{KVL})$$

$$I_B = \frac{V_{EE} - V_{BE}}{R_B} = \frac{9 - 0.7}{100k} = 83\mu A$$

$$I_C = \beta I_B = (45)(83\mu) = 3.735mA$$

$$V_C = -I_C R_C = -(3.735m)(1.2k) = -4.48V$$

$$V_B = -I_B R_B = -(83\mu)(100k) = -8.3V$$

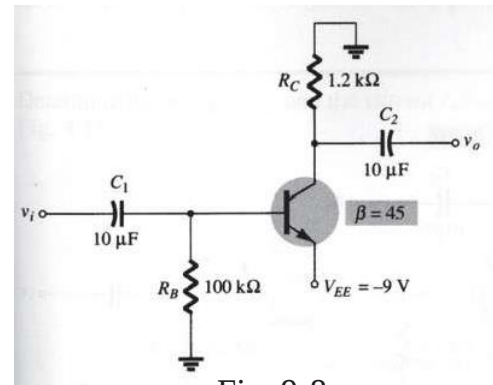


Fig. 9-8

Example 9-3: (Two Supplies)

Determine V_C and V_B for the circuit of Fig. 9-9a.

Solution:

From Fig. 9-9b:

$$R_{Th} = R_1 \parallel R_2 = 8.2k \parallel 2.2k = 1.73k\Omega$$

$$I = \frac{V_{CC} + V_{EE}}{R_1 + R_2} = \frac{20 + 20}{8.2k + 2.2k} = 3.85mA$$

$$E_{Th} = IR_2 - V_{EE} = (3.85m)(2.2k) - 20 = -11.53V$$

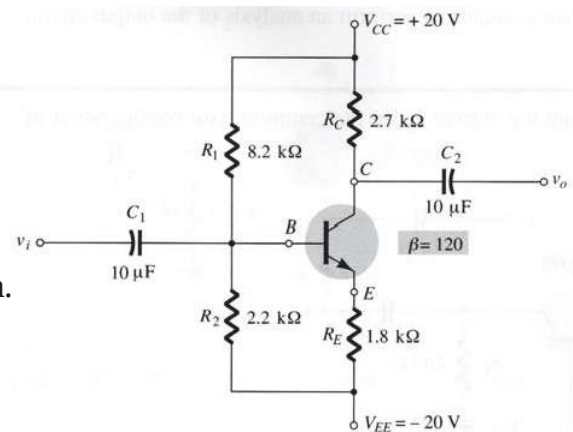
From Fig. 9-9c:

$$-E_{Th} - I_B R_{Th} - V_{BE} - I_E R_E + V_{EE} = 0 \quad (\text{KVL})$$

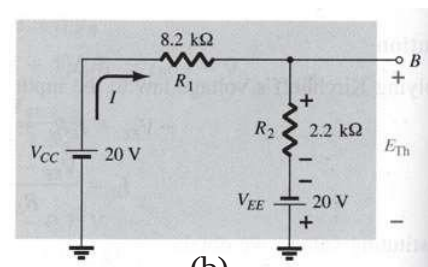
$$I_E = (\beta + 1)I_B$$

$$I_B = \frac{V_{EE} - E_{Th} - V_{BE}}{R_{Th} + (\beta + 1)R_E}$$

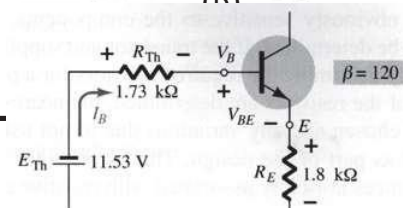
$$\frac{20 - 11.53 - 0.7}{1.73k + (120 + 1)1.8k} = 35.39\mu A$$



(a)



(b)



$$= \frac{1.73k + (121)(1.8k)}{1.73k + (121)(1.8k)} =$$

$$I_C = \beta I_B = (120)(35.39\mu) = 4.25mA$$

$$V_C = V_{CC} - I_C R_C = 20 - (4.25m)(2.7k) = 8.53V$$

$$V_B = -E_{Th} - I_B R_{Th} = -(11.53) - (35.39\mu)(1.73k)$$

$$= -11.59V$$

(c)

Fig. 9-9

Example 9-4: (Common-Base)

Determine V_{CB} and I_B for the common-base configuration of Fig. 9-10.

Solution:

Applying KVL to the input circuit:

$$-V_{EE} + I_E R_E + V_{BE} = 0$$

$$I_E = \frac{V_{EE} - V_{BE}}{R_E} = \frac{4 - 0.7}{1.2k} = 2.75mA$$

Applying KVL to the output circuit:

$$+V_{CB} + I_C R_C - V_{CC} = 0$$

$$V_{CB} = V_{CC} - I_C R_C$$

$$\text{with } I_C \cong I_E$$

$$V_{CB} = 10 - (2.75m)(2.4k) = 3.4V$$

$$I_B = \frac{I_C}{\beta} = \frac{2.75m}{60} = 45.8\mu A$$

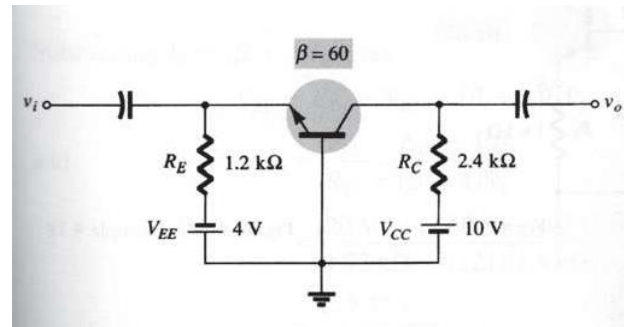


Fig. 9-10

Example 9-5: (Common-Collector)

Determine I_E and V_{CE} for the common-collector (emitter-follower) configuration of Fig. 9-11.

Solution:

Applying KVL to the input circuit:

$$-I_B R_B - V_{BE} - I_E R_E + V_{EE} = 0$$

$$I_E = (\beta + 1)I_B$$

$$I_B = \frac{V_{EE} - V_{BE}}{R_B + (\beta + 1)R_E}$$

$$= \frac{20 - 0.7}{240k + (91)(2k)} = 45.73\mu A$$

$$I_E = (\beta + 1)I_B = (91)(45.73\mu) = 4.16mA$$

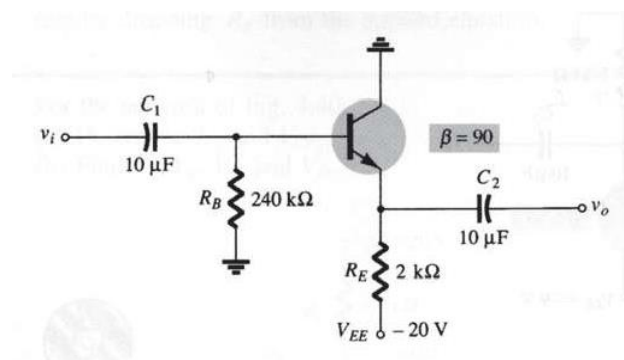


Fig. 9-11

Applying KVL to the output circuit:

$$-V_{EE} + I_E R_E + V_{CE} = 0$$

$$V_{CE} = V_{EE} - I_E R_E = 20 - (4.16m)(2k) = 11.68V$$

Example 9-6: (PNP Transistor)

Determine V_{CE} for the voltage-divider bias configuration of Fig. 9-12.

Solution:

Testing: $\beta R_E \geq 10R_2$

$$(120)(1.1k) \geq 10(10k)$$

$$132k\Omega \geq 100k\Omega \text{ (satisfied)}$$

$$V_B = \frac{R_2 V_{CC}}{R_1 + R_2} = \frac{(10k)(-18)}{47k + 10k} = -3.16V$$

$$V_E = V_B - V_{BE} = -3.16 - (-0.7) = -2.46V$$

$$I_C = I_E = \frac{V_E}{R_E} = \frac{2.46}{1.1k} = 2.24mA$$

$$-I_E R_E + V_{CE} - I_C R_C + V_{CC} = 0 \quad (\text{KVL})$$

$$V_{CE} = -V_{CC} + I_C (R_C + R_E)$$

$$= -18 + (2.24m)(2.4k + 1.1k) = -10.16V$$

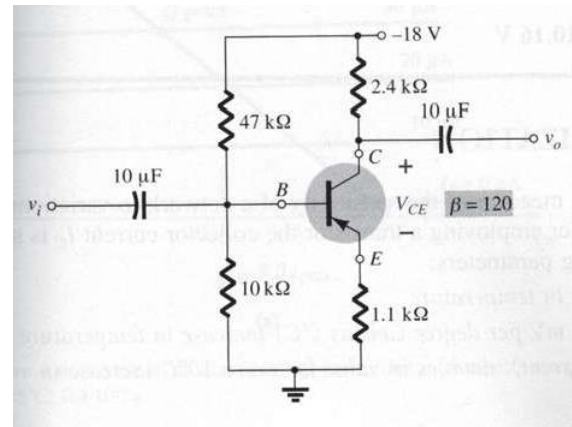


Fig. 9-12

Exercises:

- For the fixed-biased configuration of Fig. 9-2a with the following parameters: $V_{CC} = +12V$, $\beta = 50$, $R_B = 240k\Omega$, and $R_C = 2.2k\Omega$, determine: I_{BQ} , I_{CQ} , V_{CEQ} , V_B , V_C , and V_{BC} .
- Given the device characteristics of Fig. 9-13a, determine V_{CC} , R_B , and R_C for the fixed-bias configuration of Fig. 9-13b.

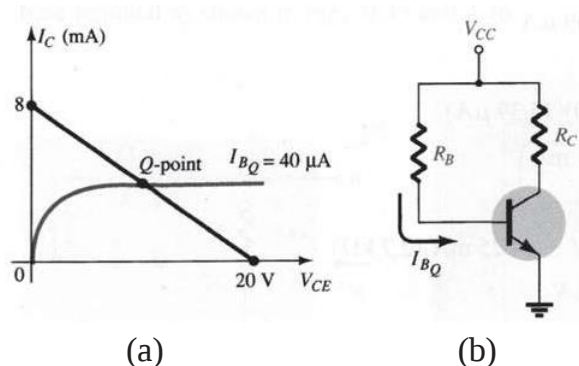


Fig. 9-13

3. For the emitter bias circuit of Fig. 9-4a with the following parameters: $V_{CC} = +20\text{ V}$, $\beta = 50$, $R_B = 430\text{ k}\Omega$, $R_C = 2\text{ k}\Omega$, and $R_E = 1\text{ k}\Omega$, determine: I_B , I_C , V_{CE} , V_C , V_E , V_B and V_{BC} .
4. Design an emitter-stabilized circuit (Fig. 9-4a) at $I_{CQ} = 2\text{ mA}$. Use $V_{CC} = +20\text{ V}$ and an npn transistor with $\beta = 150$.
5. Determine the dc bias voltage V_{CE} and the current I_C for the voltage-divider configuration of Fig. 9-6a with the following parameters: $V_{CC} = +18\text{ V}$, $\beta = 50$, $R_1 = 82\text{ k}\Omega$, $R_2 = 22\text{ k}\Omega$, $R_C = 5.6\text{ k}\Omega$, and $R_E = 1.2\text{ k}\Omega$.
6. Design a beta-independent (voltage-divider) circuit to operate at $V_{CEQ} = 8\text{ V}$ and $I_{CQ} = 10\text{ mA}$. Use a supply of $V_{CC} = +20\text{ V}$ and an npn transistor with $\beta = 80$.
7. Determine the quiescent levels of I_{CQ} and V_{CEQ} for the voltage-feedback circuit of Fig. 9-7a with the following parameters: $V_{CC} = +10\text{ V}$, $\beta = 90$, $R_B = 250\text{ k}\Omega$, $R_C = 4.7\text{ k}\Omega$, and $R_E = 1.2\text{ k}\Omega$.
8. Prove that $R_B \leq \beta(R_C + R_E)$ is the required condition for an optimum design of the voltage-feedback circuit.
9. Prove mathematically that I_{CQ} for the voltage-feedback bias circuit is approximately independent of the value of beta.
10. Fig. 9-14 shows a three-stage circuit with a V_{CC} supply of $+20\text{ V}$. GND stands for ground. If all transistors have a β of 100, what are the I_C and V_{CE} of each stage?

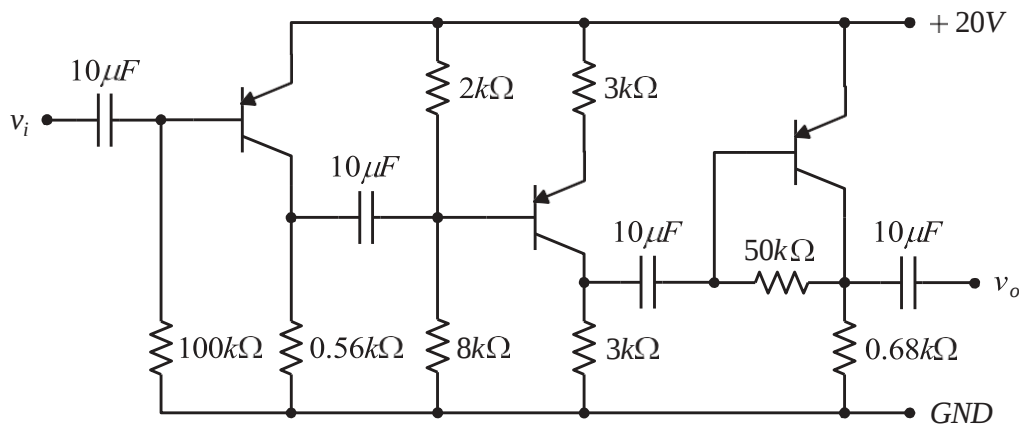


Fig. 9-14